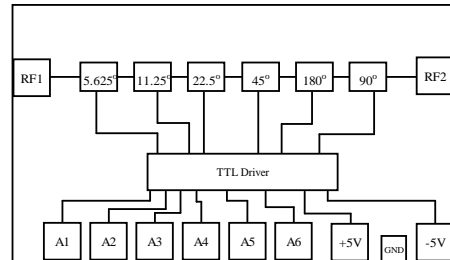


5.0 – 6.5 GHz 6-Bit Digital Phase Shifter

Features

- ◆ Frequency Range: 5 to 6.5 GHz
- ◆ RMS Error ~ 2 deg.
- ◆ 7 dB Insertion Loss
- ◆ TTL Control Inputs
- ◆ 0.5-um InGaAs pHEMT Technology
- ◆ Chip Size : 4.5mm x 2.2 mm x 0.1 mm

Functional Diagram



Typical Applications

- ◆ Radar
- ◆ Military & Space
- ◆ Instrumentation

Description

The AMT 2231022 is a 6-bit digital phase shifter MMIC designed to operate over a frequency band of 5-6.5 GHz. The phase shifter features a low RMS phase error of less than 3 deg over the entire operating band. The midband insertion loss is 7 dB and varies within ± 1.2 dB over the band and the 64 phase states. The input /output ports are well matched to 50 Ohms. The integrated TTL compatible drivers provide a convenient digital interface for 6-bit control. The chip operates with +5V and -5V DC supply at a very low current. The MMIC die is fabricated using a robust 0.5 μ m InGaAs pHEMT technology.

Absolute Maximum Ratings ⁽¹⁾

| Parameter | Absolute Maximum | Units |
|-------------------------|------------------|-------|
| RF Input Power | 30 | dBm |
| Positive Supply Voltage | +6 | V |
| Negative Supply Voltage | -6 | V |
| Control Voltage | | |
| ON | +5 to +5.5 | V |
| OFF | -0.5 to 0 | V |
| Operating Temperature | -40 to +85 | °C |
| Storage Temperature | -65 to +150 | °C |

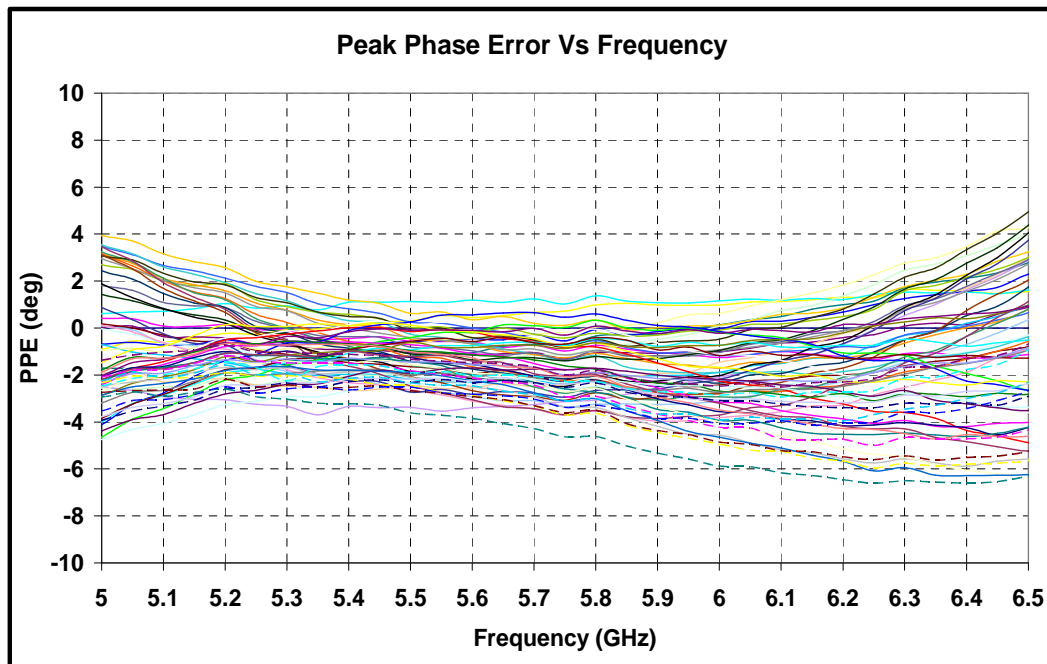
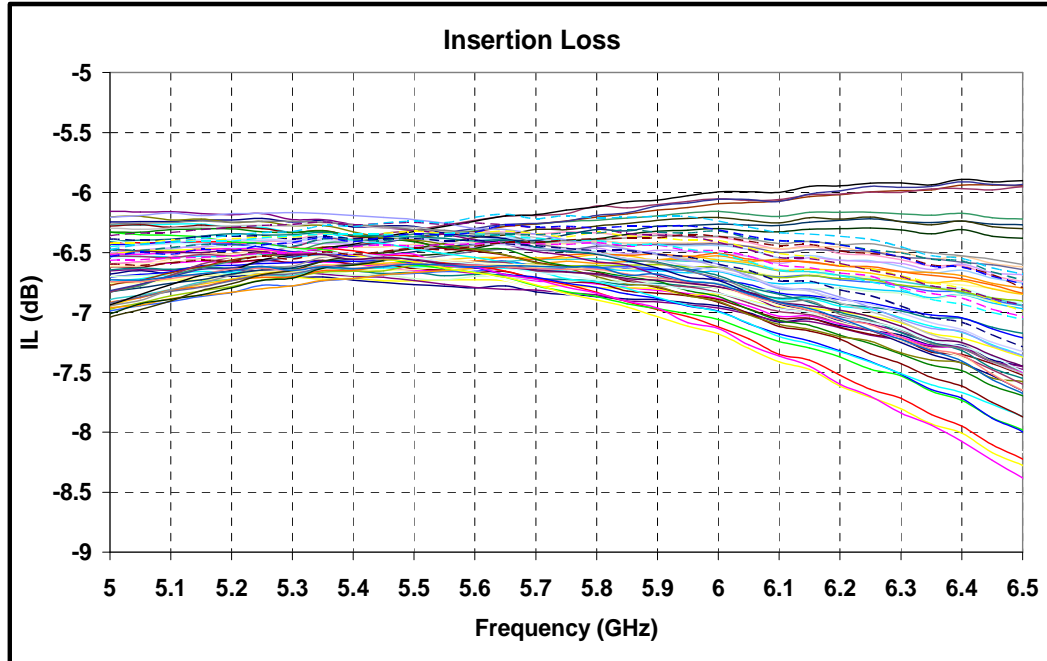
1. Operation beyond these limits may cause permanent damage to the component

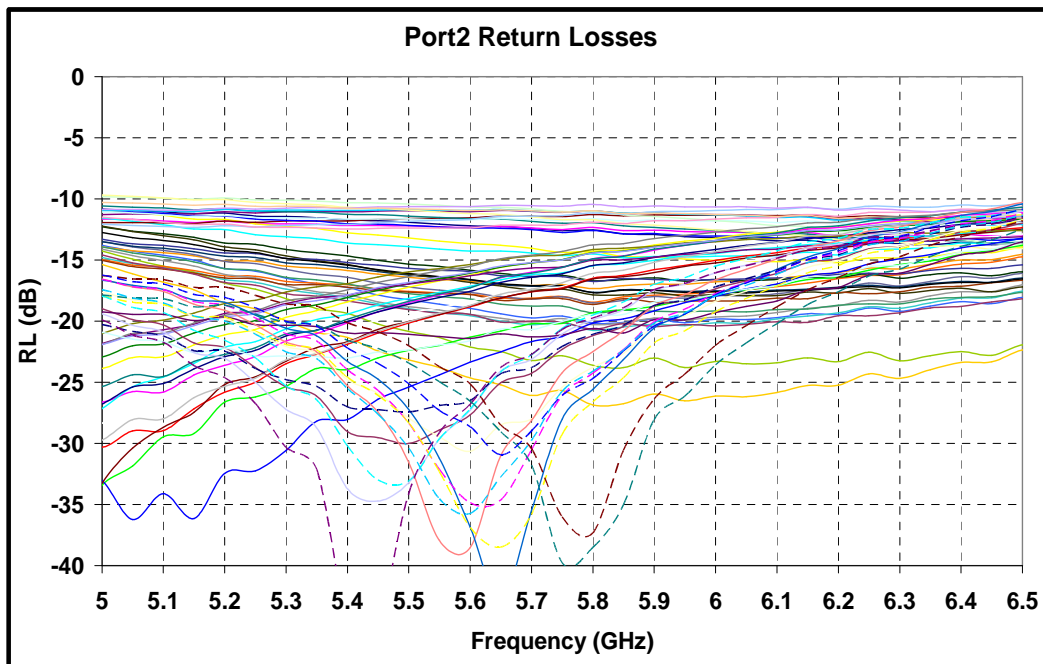
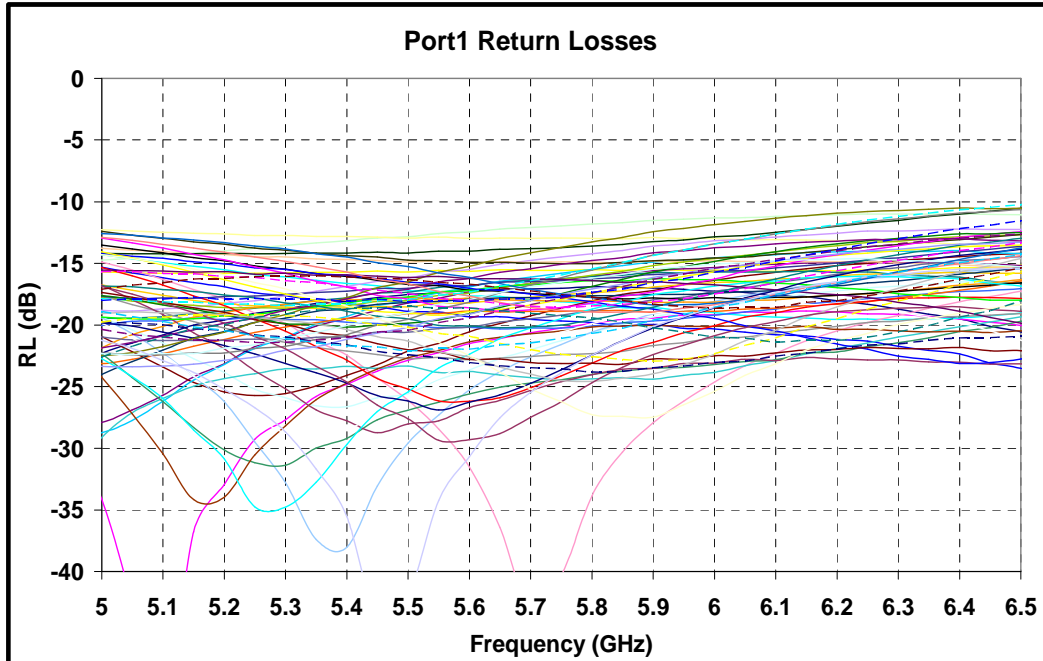
Electrical Specifications ⁽¹⁾ @ T_A = 25 °C, Z_o =50 Ω

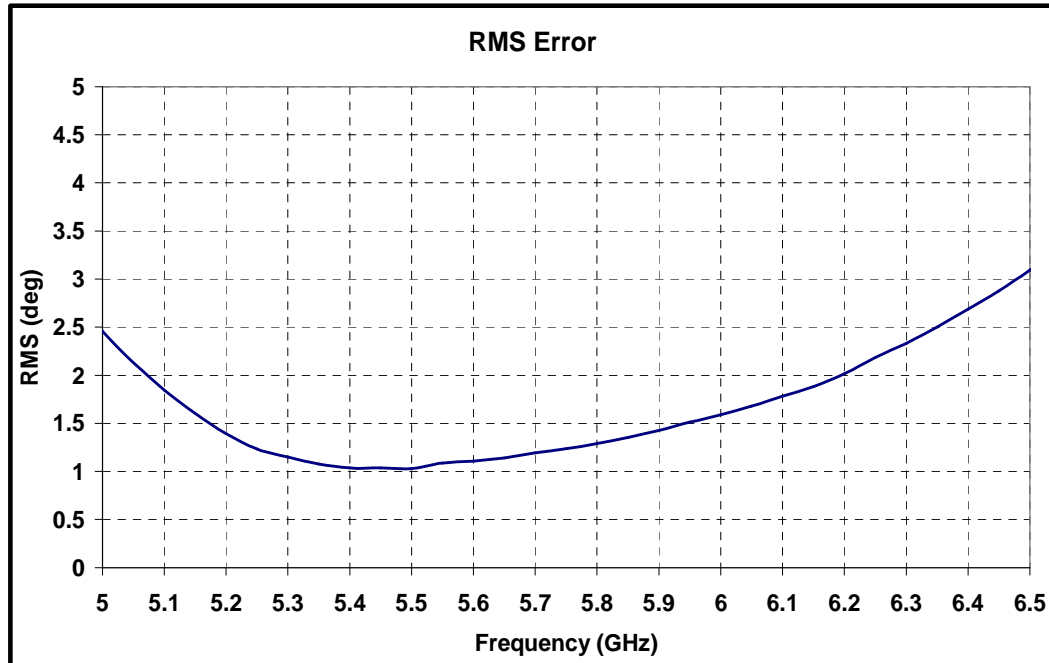
| Parameter | Value | Units |
|---|-------------------|-------|
| Frequency | 5.0 – 6.5 | GHz |
| Phase Shift | 0-360 in 64 steps | deg |
| Insertion Loss (Typ.) | 7 | dB |
| Insertion Loss Variation | ± 1.2 | dB |
| Peak Phase Error | -7 to +5 | deg |
| RMS Error | < 3.0 | deg |
| Port1 Return Loss | 10 | dB |
| Port2 Return Loss | 10 | dB |
| Pin for 1dB gain compression ⁽²⁾ | 23 | dBm |
| DC Supply | +5/6, -5/3 | V/mA |
| Control Voltage | 0 / +5 | V |

Note:

1. The above mentioned electrical specifications are measured On-Wafer.
2. Measured for Major States only.

On Wafer data $T_A = 25^\circ\text{C}$ 

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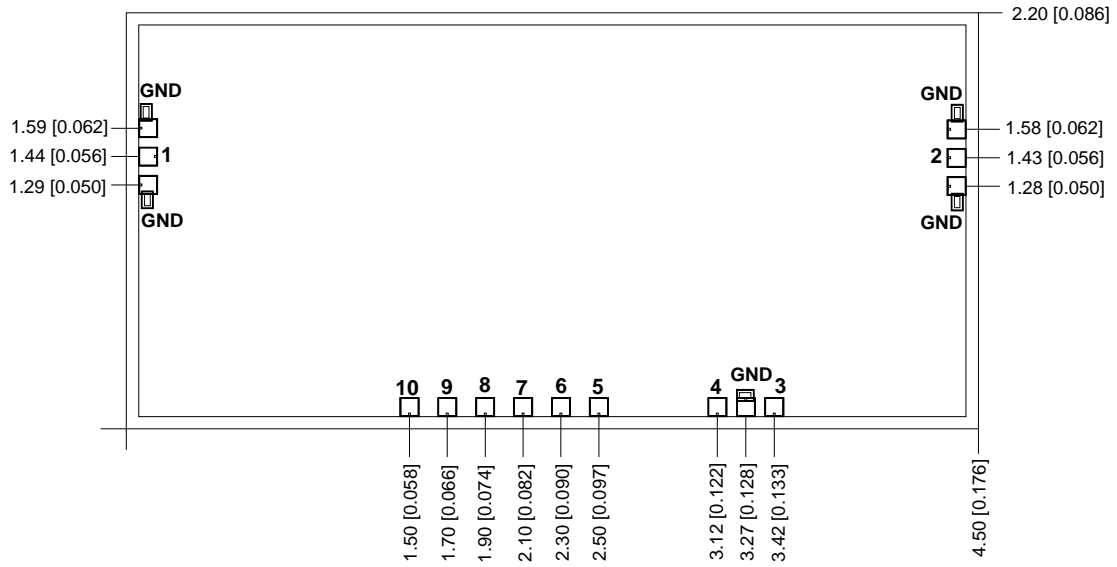
Truth Table

| State | Phase Shift (deg.) | TTL Control (1 = 3.5 to 5 V, 0 = 0 to 0.5 V) | | | | | |
|-------|--------------------|--|---------|---------|-----------|------------|------------|
| | | A6 (180) | A5 (90) | A4 (45) | A3 (22.5) | A2 (11.25) | A1 (5.625) |
| 0 | 0 | 0 | 0 | 0 | 0 | 0 | 0 |
| 1 | 5.625 | 0 | 0 | 0 | 0 | 0 | 1 |
| 2 | 11.25 | 0 | 0 | 0 | 0 | 1 | 0 |
| 3 | 16.875 | 0 | 0 | 0 | 0 | 1 | 1 |
| 4 | 22.5 | 0 | 0 | 0 | 1 | 0 | 0 |
| 5 | 28.125 | 0 | 0 | 0 | 1 | 0 | 1 |
| 6 | 33.75 | 0 | 0 | 0 | 1 | 1 | 0 |
| 7 | 39.375 | 0 | 0 | 0 | 1 | 1 | 1 |
| 8 | 45 | 0 | 0 | 1 | 0 | 0 | 0 |
| 9 | 50.625 | 0 | 0 | 1 | 0 | 0 | 1 |
| 10 | 56.25 | 0 | 0 | 1 | 0 | 1 | 0 |
| 11 | 61.875 | 0 | 0 | 1 | 0 | 1 | 1 |
| 12 | 67.5 | 0 | 0 | 1 | 1 | 0 | 0 |
| 13 | 73.125 | 0 | 0 | 1 | 1 | 0 | 1 |
| 14 | 78.75 | 0 | 0 | 1 | 1 | 1 | 0 |
| 15 | 84.375 | 0 | 0 | 1 | 1 | 1 | 1 |
| 16 | 90 | 0 | 1 | 0 | 0 | 0 | 0 |
| 17 | 95.625 | 0 | 1 | 0 | 0 | 0 | 1 |
| 18 | 101.25 | 0 | 1 | 0 | 0 | 1 | 0 |
| 19 | 106.875 | 0 | 1 | 0 | 0 | 1 | 1 |
| 20 | 112.5 | 0 | 1 | 0 | 1 | 0 | 0 |
| 21 | 118.125 | 0 | 1 | 0 | 1 | 0 | 1 |
| 22 | 123.75 | 0 | 1 | 0 | 1 | 1 | 0 |
| 23 | 129.375 | 0 | 1 | 0 | 1 | 1 | 1 |
| 24 | 135 | 0 | 1 | 1 | 0 | 0 | 0 |
| 25 | 140.625 | 0 | 1 | 1 | 0 | 0 | 1 |
| 26 | 146.25 | 0 | 1 | 1 | 0 | 1 | 0 |
| 27 | 151.875 | 0 | 1 | 1 | 0 | 1 | 1 |
| 28 | 157.5 | 0 | 1 | 1 | 1 | 0 | 0 |
| 29 | 163.125 | 0 | 1 | 1 | 1 | 0 | 1 |
| 30 | 168.75 | 0 | 1 | 1 | 1 | 1 | 0 |
| 31 | 174.375 | 0 | 1 | 1 | 1 | 1 | 1 |
| 32 | 180 | 1 | 0 | 0 | 0 | 0 | 0 |
| 33 | 185.625 | 1 | 0 | 0 | 0 | 0 | 1 |
| 34 | 191.25 | 1 | 0 | 0 | 0 | 1 | 0 |
| 35 | 196.875 | 1 | 0 | 0 | 0 | 1 | 1 |

Truth Table

| State | Phase Shift (deg.) | TTL Control (1 = 3.5 to 5 V, 0 = 0 to 0.5 V) | | | | | |
|-------|--------------------|--|---------|---------|-----------|------------|------------|
| | | A6 (180) | A5 (90) | A4 (45) | A3 (22.5) | A2 (11.25) | A1 (5.625) |
| 36 | 202.5 | 1 | 0 | 0 | 1 | 0 | 0 |
| 37 | 208.125 | 1 | 0 | 0 | 1 | 0 | 1 |
| 38 | 213.75 | 1 | 0 | 0 | 1 | 1 | 0 |
| 39 | 219.375 | 1 | 0 | 0 | 1 | 1 | 1 |
| 40 | 225 | 1 | 0 | 1 | 0 | 0 | 0 |
| 41 | 230.625 | 1 | 0 | 1 | 0 | 0 | 1 |
| 42 | 236.25 | 1 | 0 | 1 | 0 | 1 | 0 |
| 43 | 241.875 | 1 | 0 | 1 | 0 | 1 | 1 |
| 44 | 247.5 | 1 | 0 | 1 | 1 | 0 | 0 |
| 45 | 253.125 | 1 | 0 | 1 | 1 | 0 | 1 |
| 46 | 258.75 | 1 | 0 | 1 | 1 | 1 | 0 |
| 47 | 264.375 | 1 | 0 | 1 | 1 | 1 | 1 |
| 48 | 270 | 1 | 1 | 0 | 0 | 0 | 0 |
| 49 | 275.625 | 1 | 1 | 0 | 0 | 0 | 1 |
| 50 | 281.25 | 1 | 1 | 0 | 0 | 1 | 0 |
| 51 | 286.875 | 1 | 1 | 0 | 0 | 1 | 1 |
| 52 | 292.5 | 1 | 1 | 0 | 1 | 0 | 0 |
| 53 | 298.125 | 1 | 1 | 0 | 1 | 0 | 1 |
| 54 | 303.75 | 1 | 1 | 0 | 1 | 1 | 0 |
| 55 | 309.375 | 1 | 1 | 0 | 1 | 1 | 1 |
| 56 | 315 | 1 | 1 | 1 | 0 | 0 | 0 |
| 57 | 320.625 | 1 | 1 | 1 | 0 | 0 | 1 |
| 58 | 326.25 | 1 | 1 | 1 | 0 | 1 | 0 |
| 59 | 331.875 | 1 | 1 | 1 | 0 | 1 | 1 |
| 60 | 337.5 | 1 | 1 | 1 | 1 | 0 | 0 |
| 61 | 343.125 | 1 | 1 | 1 | 1 | 0 | 1 |
| 62 | 348.75 | 1 | 1 | 1 | 1 | 1 | 0 |
| 63 | 354.375 | 1 | 1 | 1 | 1 | 1 | 1 |

Mechanical Characteristics

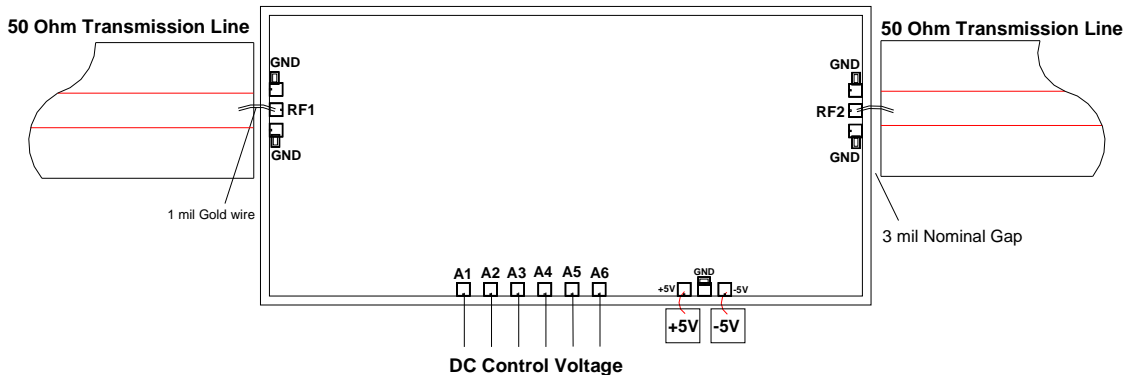


Units: millimeters (inches)

Note:

1. All RF and DC bond pads are 100µm x 100µm
2. Pad no. 1 : RF1
3. Pad no. 2 : RF2
4. Pad no. 3 : -5 V
5. Pad no. 4 : +5 V
6. Pad no. 5 to 10 : A6 to A1 (Control bits from MSB to LSB)

Recommended Assembly Diagram



Note :

1. Two 1 mil (0.0254mm) bond wires of minimum length should be used for RF input and output.
2. The RF input & output ports are DC coupled.

Die attach: For Epoxy attachment, use of a two-component conductive epoxy is recommended. An epoxy fillet should be visible around the total die periphery. If Eutectic attachment is preferred, use of fluxless AuSn (80/20) 1-2 mil thick preform solder is recommended. Use of AuGe preform should be strictly avoided.

Wire bonding: For DC pad connections use either ball or wedge bonds. For best RF performance, use of 150 - 200µm length of wedge bonds is advised. Single Ball bonds of 250-300µm though acceptable, may cause a deviation in RF performance.



GaAs MMIC devices are susceptible to Electrostatic discharge. Proper precautions should be observed during handling, assembly & testing

All information and Specifications are subject to change without prior notice